Supporting Information

An Enhanced Ultrasensitive Solar-blind UV Photodetector Based on an Asymmetric Schottky Junction Designed with Graphene/β-Ga_2O_3/Ag

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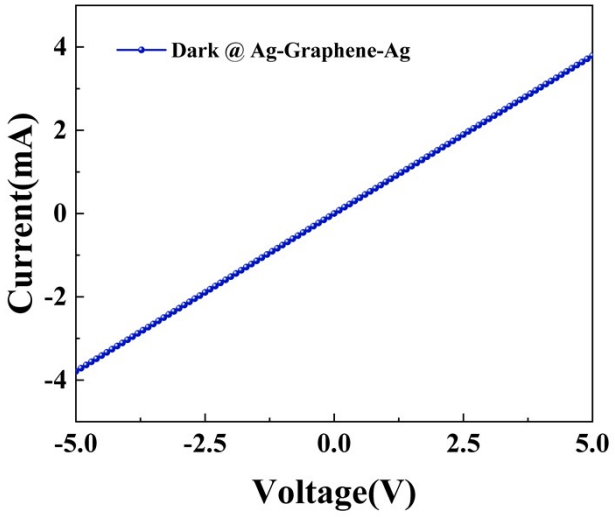

Figure S1 I–V curve of graphene with Ag electrode in the dark.

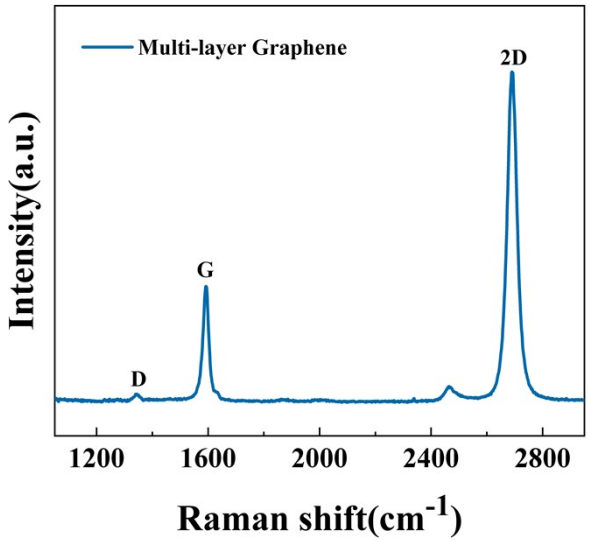

Figure S2 The Raman spectra of the multilayer graphene

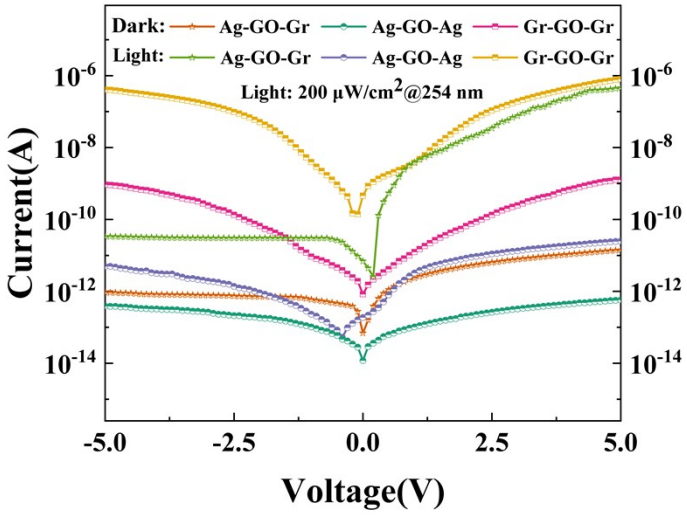

Figure S3 The I-V curves of three contacts in dark and under 254 nm UV light at a light intensity of 200μW/cm^2.

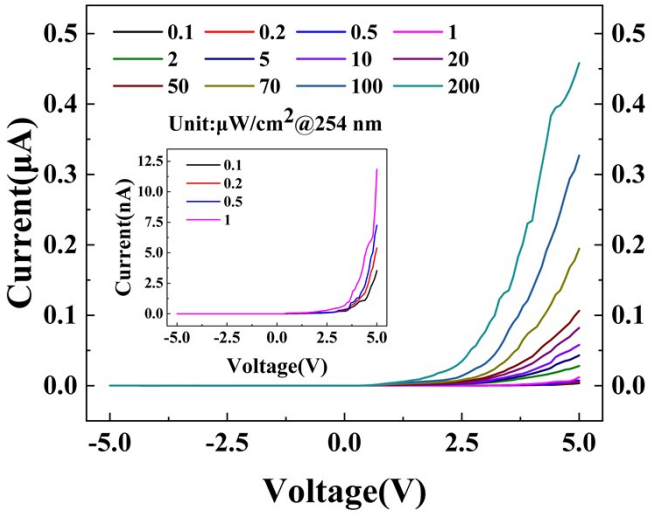

Figure S4 I−V curves of the device under various light illumination.

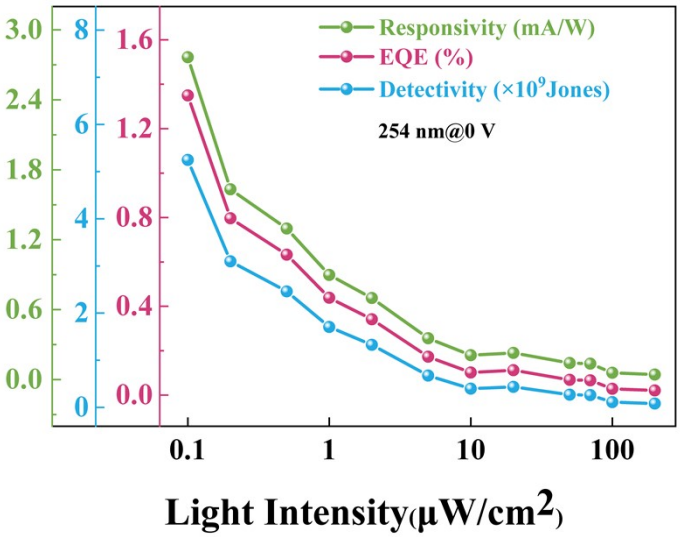

Figure S5 Responsivity, Detectivity and EQE of the device under different light intensities of 254 nm UV light illumination at 0V bias.

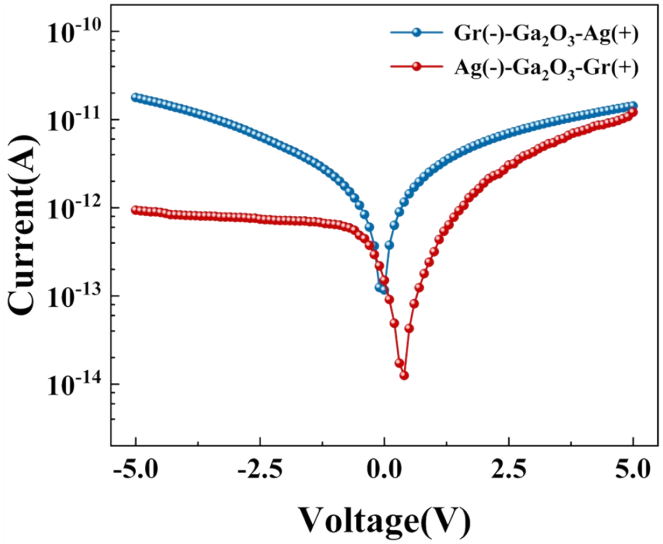

Figure S6 Dark current of the device when applying forward and reverse voltages.